

Joseph Kioseoglou

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122
papers

1,269
citations

19
h-index

29
g-index

129
ext. papers

1,428
ext. citations

3.9
avg, IF

4.47
L-index

| # | Paper | IF | Citations |
|-----|---|------|-----------|
| 122 | Selective area growth of well-ordered ZnO nanowire arrays with controllable polarity. <i>ACS Nano</i> , 2014 , 8, 4761-70 | 16.7 | 70 |
| 121 | Kinetic trapping through coalescence and the formation of patterned Ag-Cu nanoparticles. <i>Nanoscale</i> , 2016 , 8, 9780-90 | 7.7 | 61 |
| 120 | Indium migration paths in V-defects of InAlN grown by metal-organic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2009 , 95, 071905 | 3.4 | 60 |
| 119 | Nanostructure and strain in InGaN/GaN superlattices grown in GaN nanowires. <i>Nanotechnology</i> , 2013 , 24, 435702 | 3.4 | 49 |
| 118 | Mechanism of compositional modulations in epitaxial InAlN films grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2009 , 95, 021913 | 3.4 | 46 |
| 117 | Computational Modeling of Nanoparticle Coalescence. <i>Advanced Theory and Simulations</i> , 2019 , 2, 19000135 | 3.5 | 44 |
| 116 | A modified empirical potential for energetic calculations of planar defects in GaN. <i>Computational Materials Science</i> , 2003 , 27, 43-49 | 3.2 | 39 |
| 115 | Dislocation core investigation by geometric phase analysis and the dislocation density tensor. <i>Journal Physics D: Applied Physics</i> , 2008 , 41, 035408 | 3 | 37 |
| 114 | Intrinsic point defects in buckled and puckered arsenene: a first-principles study. <i>Physical Chemistry Chemical Physics</i> , 2017 , 19, 9862-9871 | 3.6 | 36 |
| 113 | Atomic-resolution imaging of surface and core melting in individual size-selected Au nanoclusters on carbon. <i>Nature Communications</i> , 2019 , 10, 2583 | 17.4 | 27 |
| 112 | Atomic structures and energies of partial dislocations in wurtzite GaN. <i>Physical Review B</i> , 2004 , 70, | 3.3 | 27 |
| 111 | Structural transition of inversion domain boundaries through interactions with stacking faults in epitaxial GaN. <i>Physical Review B</i> , 2001 , 64, | 3.3 | 24 |
| 110 | Hole-Doped 2D InSe for Spintronic Applications. <i>ACS Applied Nano Materials</i> , 2018 , 1, 6656-6665 | 5.6 | 23 |
| 109 | Effect of edge threading dislocations on the electronic structure of InN. <i>Applied Physics Letters</i> , 2011 , 98, 072103 | 3.4 | 22 |
| 108 | Hydrogen Flux through Size Selected Pd Nanoparticles into Underlying Mg Nanofilms. <i>Advanced Energy Materials</i> , 2018 , 8, 1701326 | 21.8 | 21 |
| 107 | Partial dislocations in wurtzite GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 2888-2899 | 1.6 | 21 |
| 106 | Morphology and strain of self-assembled semipolar GaN quantum dots in (112̄) AlN. <i>Journal of Applied Physics</i> , 2010 , 108, 104304 | 2.5 | 20 |

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|-----|--|------|----|
| 105 | Analysis of partial dislocations in wurtzite GaN using gradient elasticity. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 2161-2166 | 1.6 | 20 |
| 104 | Thermal Oxidation of Size-Selected Pd Nanoparticles Supported on CuO Nanowires: The Role of the CuO/Pd Interface. <i>Chemistry of Materials</i> , 2017 , 29, 6153-6160 | 9.6 | 19 |
| 103 | Tuning the onset of ferromagnetism in heterogeneous bimetallic nanoparticles by gas phase doping. <i>Physical Review Materials</i> , 2017 , 1, | 3.2 | 19 |
| 102 | Misfit reduction by a spinel layer formed during the epitaxial growth of ZnO on sapphire using a MgO buffer layer. <i>Journal of Crystal Growth</i> , 2007 , 308, 314-320 | 1.6 | 18 |
| 101 | Interatomic potential calculations of III(Al, In)N planar defects with a III-species environment approach. <i>Physica Status Solidi (B): Basic Research</i> , 2008 , 245, 1118-1124 | 1.3 | 18 |
| 100 | Broad compositional tunability of indium tin oxide nanowires grown by the vapor-liquid-solid mechanism. <i>APL Materials</i> , 2014 , 2, 056104 | 5.7 | 17 |
| 99 | Polar AlN/GaN interfaces: Structures and energetics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1892-1897 | 1.6 | 17 |
| 98 | Observation of Metal to Metal Oxide Progression: A Study of Charge Transfer Phenomenon at Ru-CuO Interfaces. <i>ACS Nano</i> , 2019 , 13, 12425-12437 | 16.7 | 16 |
| 97 | Impact of screw and edge dislocations on the thermal conductivity of individual nanowires and bulk GaN: a molecular dynamics study. <i>Physical Chemistry Chemical Physics</i> , 2018 , 20, 5159-5172 | 3.6 | 16 |
| 96 | Electronic structure of 1/6$\langle 111 \bar{2}00 \rangle$ partial dislocations in wurtzite GaN. <i>Journal of Applied Physics</i> , 2011 , 109, 083511 | 2.5 | 15 |
| 95 | Zinc Vacancy-Hydrogen Complexes as Major Defects in ZnO Nanowires Grown by Chemical Bath Deposition. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 16652-16662 | 3.8 | 14 |
| 94 | Screw threading dislocations in AlN: Structural and electronic properties of In and O doped material. <i>Journal of Applied Physics</i> , 2011 , 110, 053715 | 2.5 | 13 |
| 93 | Study of InN/GaN interfaces using molecular dynamics. <i>Journal of Materials Science</i> , 2008 , 43, 3982-3988 | 4.3 | 13 |
| 92 | Core models of a-edge threading dislocations in wurtzite III(Al,Ga,In)-nitrides. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1931-1935 | 1.6 | 12 |
| 91 | Structural and electronic properties of GaN nanowires with embedded In _x Ga _{1-x} N nanodisks. <i>Journal of Applied Physics</i> , 2015 , 118, 034301 | 2.5 | 11 |
| 90 | 3D modelling of misfit networks in the interface region of heterostructures. <i>Journal Physics D: Applied Physics</i> , 2007 , 40, 4084-4091 | 3 | 11 |
| 89 | Strain distribution of thin InN epilayers grown on (0001) GaN templates by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2007 , 90, 061920 | 3.4 | 11 |
| 88 | Microstructural assessment of InN-on-GaN films grown by plasma-assisted MBE. <i>Superlattices and Microstructures</i> , 2004 , 36, 509-515 | 2.8 | 11 |

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|----|---|-----|----|
| 87 | Microstructure of planar defects and their interactions in wurtzite GaN films. <i>Solid-State Electronics</i> , 2003 , 47, 553-557 | 1.7 | 11 |
| 86 | Single Nanoparticle Activities in Ensemble: A Study on Pd Cluster Nanoportals for Electrochemical Oxygen Evolution Reaction. <i>Journal of Physical Chemistry C</i> , 2019 , 123, 26124-26135 | 3.8 | 10 |
| 85 | Effect of the lower and upper interfaces on the quality of InAs/GaAs quantum dots. <i>Applied Surface Science</i> , 2014 , 301, 173-177 | 6.7 | 10 |
| 84 | Nonsingular dislocation and crack fields: implications to small volumes. <i>Microsystem Technologies</i> , 2009 , 15, 117-121 | 1.7 | 10 |
| 83 | Junction lines of inversion domain boundaries with stacking faults in GaN. <i>Physical Review B</i> , 2004 , 70, | 3.3 | 10 |
| 82 | Observation of the Direct Energy Band Gaps of Defect-Tolerant Cu ₃ N by Ultrafast Pump-Probe Spectroscopy. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 3459-3469 | 3.8 | 9 |
| 81 | Ultrafast pulsed laser deposition of carbon nanostructures: Structural and optical characterization. <i>Applied Surface Science</i> , 2013 , 278, 101-105 | 6.7 | 9 |
| 80 | Structural properties of SnO ₂ nanowires and the effect of donor like defects on its charge distribution. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 226-229 | 1.6 | 9 |
| 79 | Strain relaxation in AlN/GaN heterostructures grown by molecular beam epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2569-2572 | 1.6 | 9 |
| 78 | Energetics of the Shockley partial dislocation in wurtzite GaN. <i>Superlattices and Microstructures</i> , 2006 , 40, 458-463 | 2.8 | 9 |
| 77 | Enhanced Stark Tuning of Single InAs (211)B Quantum Dots due to Nonlinear Piezoelectric Effect in Zincblende Nanostructures. <i>Physical Review Applied</i> , 2016 , 6, | 4.3 | 8 |
| 76 | Ordered structures in III-Nitride ternary alloys. <i>Computational Materials Science</i> , 2016 , 118, 22-31 | 3.2 | 8 |
| 75 | Atomic scale modeling of edge a-type dislocations in InN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 204-208 | 1.6 | 8 |
| 74 | MOVPE prepared InAs/GaAs quantum dots covered by GaAsSb layer with long wavelength emission at 1.8 μ m. <i>Journal of Crystal Growth</i> , 2015 , 414, 167-171 | 1.6 | 8 |
| 73 | Combined vertically correlated InAs and GaAsSb quantum dots separated by triangular GaAsSb barrier. <i>Journal of Applied Physics</i> , 2013 , 114, 174305 | 2.5 | 8 |
| 72 | Mixed partial dislocation core structure in GaN by high resolution electron microscopy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 2156-2160 | 1.6 | 8 |
| 71 | Atomic-scale models of interactions between inversion domain boundaries and intrinsic basal stacking faults in GaN. <i>Diamond and Related Materials</i> , 2002 , 11, 905-909 | 3.5 | 8 |
| 70 | Microstructure of GaN Films Grown by RF-Plasma Assisted Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 639, 3471 | | 8 |

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|----|---|-----|---|
| 69 | Enhanced thermal conductivity in percolating nanocomposites: a molecular dynamics investigation. <i>Nanoscale</i> , 2018 , 10, 21732-21741 | 7.7 | 8 |
| 68 | Mechanism and crucial parameters on GaN nanocluster formation in a silica matrix. <i>Journal of Applied Physics</i> , 2017 , 121, 054301 | 2.5 | 7 |
| 67 | Endotaxially stabilized B2-FeSi nanodots in Si (100) via ion beam co-sputtering. <i>Applied Physics Letters</i> , 2014 , 104, 161903 | 3.4 | 7 |
| 66 | Reconstructions and electronic structure of (112 $\bar{2}$) and (112 $\bar{2}$) semipolar AlN surfaces. <i>Journal of Applied Physics</i> , 2012 , 112, 033510 | 2.5 | 7 |
| 65 | Defect characterization and analysis of III-V nanowires grown by Ni-promoted MBE. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2589-2592 | 1.6 | 7 |
| 64 | Interfacial and defect structures in multilayered GaN/AlN films. <i>Journal of Physics Condensed Matter</i> , 2002 , 14, 13277-13283 | 1.8 | 7 |
| 63 | The influence of structural characteristics on the electronic and thermal properties of GaN/AlN core/shell nanowires. <i>Journal of Applied Physics</i> , 2016 , 119, 074304 | 2.5 | 7 |
| 62 | Microstructure of N-face InN grown on Si (111) by plasma-assisted MBE using a thin GaN/AlN buffer layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 1074-1078 | 1.6 | 6 |
| 61 | Electron microscopy investigation of extended defects in a-plane gallium nitride layers grown on r-plane sapphire by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 3748-3751 | | 6 |
| 60 | Structure, strain, and composition profiling of InAs/GaAs(211)B quantum dot superlattices. <i>Journal of Applied Physics</i> , 2016 , 119, 034304 | 2.5 | 6 |
| 59 | Nanoassemblies of ultrasmall clusters with remarkable activity in carbon dioxide conversion into C1 fuels. <i>Nanoscale</i> , 2019 , 11, 4683-4687 | 7.7 | 6 |
| 58 | Strain and elastic constants of GaN and InN. <i>Computational Condensed Matter</i> , 2017 , 10, 25-30 | 1.7 | 5 |
| 57 | Decorated Dislocations against Phonon Propagation for Thermal Management. <i>ACS Applied Energy Materials</i> , 2020 , 3, 2682-2694 | 6.1 | 5 |
| 56 | Nanostructure and strain properties of core-shell GaAs/AlGaAs nanowires. <i>Semiconductor Science and Technology</i> , 2015 , 30, 114012 | 1.8 | 5 |
| 55 | Self-annihilation of inversion domains by high energy defects in III-Nitrides. <i>Applied Physics Letters</i> , 2014 , 104, 141914 | 3.4 | 5 |
| 54 | Atomistic modeling and HRTEM analysis of misfit dislocations in InN/GaN heterostructures. <i>Applied Surface Science</i> , 2012 , 260, 23-28 | 6.7 | 5 |
| 53 | Strain accommodation and interfacial structure of AlN interlayers in GaN. <i>Crystal Research and Technology</i> , 2009 , 44, 1170-1180 | 1.3 | 5 |
| 52 | Machine-learning interatomic potential for W-Mo alloys. <i>Journal of Physics Condensed Matter</i> , 2021 , 33, | 1.8 | 5 |

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|----|--|------|---|
| 51 | Impact of Oxygen on the Properties of Cu ₃ N and Cu ₃ N _{1-x} O _x . <i>Journal of Physical Chemistry C</i> , 2021 , 125, 3680-3688 | 3.8 | 5 |
| 50 | Energetic, structural and electronic properties of metal vacancies in strained AlN/GaN interfaces. <i>Journal of Physics Condensed Matter</i> , 2015 , 27, 125006 | 1.8 | 4 |
| 49 | Structural and electronic properties of elastically strained InN/GaN quantum well multilayer heterostructures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 289-292 | | 4 |
| 48 | Si nanostructures grown by picosecond high repetition rate pulsed laser deposition. <i>Applied Surface Science</i> , 2013 , 278, 67-70 | 6.7 | 4 |
| 47 | Ab initio investigation of the AlN:Er system. <i>Computational Materials Science</i> , 2017 , 138, 128-134 | 3.2 | 4 |
| 46 | Interfaces between nonpolar and semipolar III-nitride semiconductor orientations: Structure and defects. <i>Journal of Applied Physics</i> , 2012 , 111, 033507 | 2.5 | 4 |
| 45 | Indium adsorption and incorporation mechanisms in AlN. <i>Journal of Materials Science</i> , 2011 , 46, 4377-4383 | 4.3 | 4 |
| 44 | Twin formation in sputter-grown ZnO/Al ₂ O ₃ (0001) epitaxial film: A real time x-ray scattering study. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004 , 22, 2159-2162 | 2.9 | 4 |
| 43 | Data-driven simulation and characterisation of gold nanoparticle melting. <i>Nature Communications</i> , 2021 , 12, 6056 | 17.4 | 4 |
| 42 | Structural and electronic properties of a-edge dislocations along <1-100> in GaN. <i>Journal of Applied Physics</i> , 2018 , 123, 244301 | 2.5 | 4 |
| 41 | Ab-initio electronic structure calculations and properties of [SixSn1-x]3N4 ternary nitrides. <i>Thin Solid Films</i> , 2016 , 613, 43-47 | 2.2 | 3 |
| 40 | Epitaxially Oriented Sn:In ₂ O ₃ Nanowires Grown by the Vapor-Liquid-Solid Mechanism on m-, r-, a-Al ₂ O ₃ as Scaffolds for Nanostructured Solar Cells. <i>ACS Applied Energy Materials</i> , 2019 , 2, 4274-4283 | 6.1 | 3 |
| 39 | Structural, Electronic and Vibrational Properties of Al ₄ C ₃ . <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1900037 | 1.3 | 3 |
| 38 | Electron energy loss near edge structure of In _x Al _{1-x} N alloys. <i>Microelectronic Engineering</i> , 2013 , 112, 198-203 | 2.5 | 3 |
| 37 | Nanostructural and electronic properties of polytypes in InN nanocolumns. <i>Journal of Applied Physics</i> , 2013 , 114, 074312 | 2.5 | 3 |
| 36 | Magnesium adsorption and incorporation in InN (0001) and surfaces: A first-principles study. <i>Applied Surface Science</i> , 2009 , 255, 8475-8482 | 6.7 | 3 |
| 35 | Engineering nitrogen- and hydrogen-related defects in ZnO nanowires using thermal annealing. <i>Physical Review Materials</i> , 2021 , 5, | 3.2 | 3 |
| 34 | quantum transport in AB-stacked bilayer penta-silicene using atomic orbitals.. <i>RSC Advances</i> , 2018 , 8, 34041-34046 | 3.7 | 3 |

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|----|---|------|---|
| 33 | Structural and magnetic properties of SmCo ₅ Ni _x intermetallic compounds. <i>Journal of Alloys and Compounds</i> , 2021 , 882, 160699 | 5.7 | 3 |
| 32 | Core properties and the role of screw dislocations in the bulk n-type conductivity in InN. <i>Physical Chemistry Chemical Physics</i> , 2019 , 21, 15767-15778 | 3.6 | 2 |
| 31 | Atomic scale morphology, growth behaviour and electronic properties of semipolar {101 $\bar{1}$ } GaN surfaces. <i>Journal of Physics Condensed Matter</i> , 2013 , 25, 045008 | 1.8 | 2 |
| 30 | Effect of doping on screw threading dislocations in AlN and their role as conductive nanowires. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 484-487 | | 2 |
| 29 | Energetics of oxygen adsorption and incorporation at InN polar surface: A first-principles study. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S364-S367 | | 2 |
| 28 | Microstructure of defects in InGaN/GaN quantum well heterostructures. <i>Journal of Physics: Conference Series</i> , 2008 , 126, 012048 | 0.3 | 2 |
| 27 | Atomic simulations and HRTEM observations of a 18° tilt grain boundary in GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 799-803 | 1.6 | 2 |
| 26 | First-principles calculations of threading screw dislocations in AlN and InN. <i>Physical Review Materials</i> , 2018 , 2, | 3.2 | 2 |
| 25 | Machine Learning in Magnetic Materials. <i>Physica Status Solidi (B): Basic Research</i> , 2021 , 258, 2000600 | 1.3 | 2 |
| 24 | Interfacial properties of self-assembled GaN nanowires on pre-processed Al ₂ O ₃ (0001) surfaces. <i>Materials Science in Semiconductor Processing</i> , 2016 , 55, 46-50 | 4.3 | 2 |
| 23 | Large out-of-plane piezoelectric response of wurtzite InN under biaxial strain. <i>Modelling and Simulation in Materials Science and Engineering</i> , 2021 , 29, 065013 | 2 | 2 |
| 22 | Hydrogen Storage: Hydrogen Flux through Size Selected Pd Nanoparticles into Underlying Mg Nanofilms (Adv. Energy Mater. 4/2018). <i>Advanced Energy Materials</i> , 2018 , 8, 1870016 | 21.8 | 1 |
| 21 | Thermal oxidation and facet-formation mechanisms of Si nanowires. <i>Physica Status Solidi - Rapid Research Letters</i> , 2014 , 8, 307-311 | 2.5 | 1 |
| 20 | Structural and electronic properties of InGaN/GaN nanowires by the use of EELS. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 105-108 | | 1 |
| 19 | Atomic structure and energy of junctions between inversion domain boundaries and stacking faults in wurtzite GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2464-2469 | | 1 |
| 18 | Interaction Between Basal Stacking Faults and Prismatic Inversion Domain Boundaries in GaN. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 639, 3441 | | 1 |
| 17 | p-Type Iodine-Doping of Cu ₃ N and Its Conversion to CuI for the Fabrication of CuI/Cu ₃ N p-n Heterojunctions. <i>Electronic Materials</i> , 2022 , 3, 15-26 | 0.8 | 1 |
| 16 | The Metalorganic Vapour Phase Epitaxy Growth of AlIBVHeterostructures Observed by Reflection Anisotropy Spectroscopy. <i>Acta Physica Polonica A</i> , 2016 , 129, A-75-A-78 | 0.6 | 1 |

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|----|--|-----|---|
| 15 | Emergence of valley selectivity in monolayer tin(II) sulphide. <i>Nanoscale Advances</i> , 2019 , 1, 4863-4869 | 5.1 | 1 |
| 14 | 3-D Strain Fields in Low-Dimensional III-V Semiconductors: A Combined Finite Elements and HRTEM Approach. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700409 | 1.6 | 1 |
| 13 | Modulating the growth of chemically deposited ZnO nanowires and the formation of nitrogen- and hydrogen-related defects using pH adjustment. <i>Nanoscale Advances</i> , 2022 , 4, 1793-1807 | 5.1 | 1 |
| 12 | NanoMaterialsCAD: Flexible Software for the Design of Nanostructures. <i>Advanced Theory and Simulations</i> , 2021 , 4, 2000232 | 3.5 | 0 |
| 11 | Quantitative evaluation of the (211)B GaAs/InAs quantum dot heterostructure 2016 , 588-589 | | |
| 10 | Strain field determination in III-V heteroepitaxy coupling finite elements with experimental and theoretical techniques at the nanoscale. <i>Journal of the Mechanical Behavior of Materials</i> , 2017 , 26, 1-8 | 1.9 | |
| 9 | Nonlinear Finite Element and Atomistic Modelling of Dislocations in Heterostructures. <i>Advanced Structured Materials</i> , 2010 , 239-253 | 0.6 | |
| 8 | Electron Microscopy Characterization of a Graded AlN/GaN Multilayer Grown by Plasma-Assisted MBE. <i>Springer Proceedings in Physics</i> , 2008 , 66-68 | 0.2 | |
| 7 | Crystallization of amorphous silicon thin films: comparison between experimental and computer simulation results. <i>Journal of Materials Science</i> , 2008 , 43, 3976-3981 | 4.3 | |
| 6 | Structural properties of quaternary InAlGaIn MQW grown by plasma-assisted MBE. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 2151-2155 | 1.6 | |
| 5 | Modeling the structural characterization of nanostructures. <i>Frontiers of Nanoscience</i> , 2020 , 17, 207-227 | 0.7 | |
| 4 | Misfit analysis of the InN/GaN interface through HRTEM image simulations 2008 , 651-652 | | |
| 3 | Structural Properties and Defects of III-Nitride Semiconductors at the Nanoscale 2017 , 237-277 | | |
| 2 | Ab Initio Study of the Electron-Phonon Coupling in Ultrathin Al Layers. <i>Journal of Low Temperature Physics</i> , 2021 , 203, 180-193 | 1.3 | |
| 1 | Cost effective modification of SmCo5-type alloys. <i>AIP Advances</i> , 2022 , 12, 035343 | 1.5 | |